



FRED Ultrafast Soft Recovery Diode 2 x 30A / 600V

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating conditions
- Designed and qualified for industrial level
- Planar FRED Chip

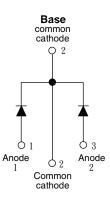
BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

HFA60PA60C is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600V and 30A per leg continuous current, the HFA60PA60C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the FRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The FRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These FRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The FRED HFA60PA60C is ideally suited for applications in power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.





PRODUCT SUMMARY					
V _R	600 V				
V _F at 30A at 25 °C	1.7 V				
I _{F(AV)}	2 x 30 A				
t _{rr} (typical)	25 ns				
T _J (maximum)	175 °C				
Q _{rr} (typical)	130 nC				
I _{RRM} (typical)	3.0 A				

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward currentper leg	I	T _C = 115 °C	30				
per device	I _F		60	А			
Single pulse forward current	I _{FSM}		300				
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 175	°C			





ELECTRICAL SPECIFICA	L SPECIFICATIONS (T _J = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-	
Maximum forward voltage	V _{FM}	I _F = 30 A	-	1.4	1.7	V
		I _F = 60 A	-	1.7	2.0	
		I _F = 30 A, T _J = 125 °C	-	1.1	1.4	
Maximum reverse Ireakage current Ireakage Current	low	$V_R = V_R$ rated	-	1.0	10	μA
	'RIM	$T_J = 150V_R = V_R$ rated	-	-	500	μΑ
Junction capacitance	CT	V _R = 200V	-	36	-	pF

DYNAMIC RECOVERY CHARACTERISTICS PERLEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS			TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	I _F = 0.5A, I _R = 1.0A, I _{RR} = 0.25A (RG#1 CKT)		-	32	38	ns
		I_F = 1.0 A, dI _F /dt = 100 A/µs, V _R =30 V, T _J = 25°C		-	25	-	
	t _{rr1}	T _J = 25 °C	I _F = 30A dI _F /dt = 200 A/μs V _R = 400 V	-	30	50	- 115
	t _{rr2}	T _J = 125 °C		-	175	-	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	3	-	A
	I _{RRM2}	T _J = 125 °C		-	6	-	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	130	-	nC
	Q _{rr2}	T _J = 125 °C		-	485	-	

THERMAL - MECHANICAL SPECIFICATIONS PER LEG							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Junction to case, single leg conduction	P		-	-	0.8		
Junction to case, both legs conducting			-	-	0.4		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-		
Weight			-	6.0	-	g	
			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf . cm (lbf . in)	
Marking device		Case style TO-247AB (JEDEC)	HFA60PA60C				



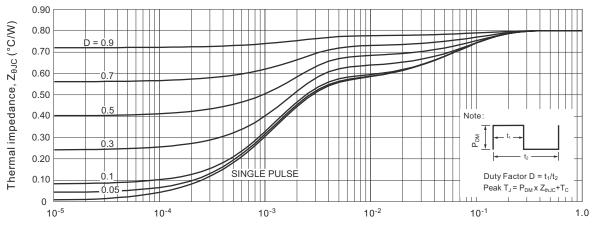


Fig.1 Maximum effective transient thermal impedance, junction-to-case vs. pulse duration

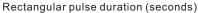
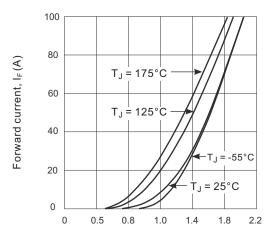
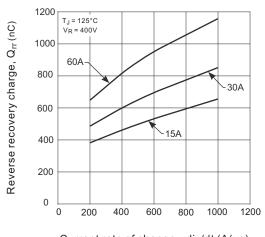


Fig.2 Forward current vs. forward voltage



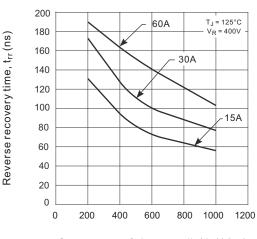
Anode-to-cathode voltage, V_F(V)





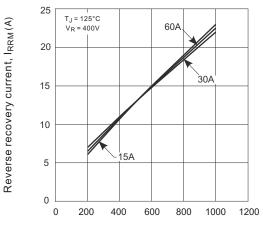
Current rate of change, -di_F/dt (A/µs)

Fig.3 Reverse recovery time vs. current rate of change



Current rate of change, $-di_F/dt (A/\mu s)$

Fig 5. Reverse recovery current vs. current rate of change



Current rate of change (A/ μ s), -di_F/dt



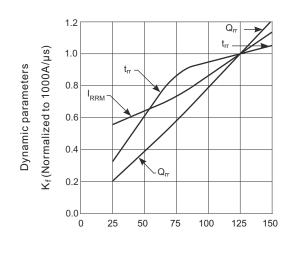
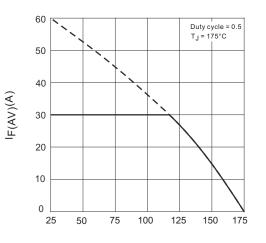


Fig6. Dynamic parameters vs. junction temperature

Junction temperature, T_J (°C)

Fig.7 Maximum average forward current vs. case temperature



Case temperature (°C)

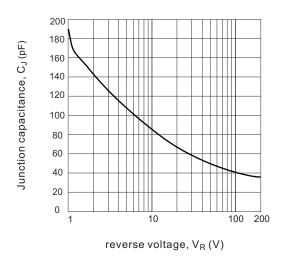


Fig.8 Junction capacitance vs. reverse voltage





ORDERING INFORMATION TABLE

